

ABSTRACT OF THE DISCLOSURE

5 A method of manufacturing a semiconductor device  
according to this invention is characterized by  
including the steps of a) forming, on one major surface  
of a substrate, a gate structure constituted by either  
one of a dummy gate electrode and a gate electrode  
having an insulating film at least on bottom surface,  
and a device isolation insulating film so as to form a  
first groove divided by the dummy gate electrode or the  
10 gate electrode, to position the dummy gate electrode or  
the gate electrode in the first groove, and to form the  
gate structure to have an upper surface level not  
higher than an upper level of the device isolation  
insulating film, and b) forming source and drain  
15 electrodes in the first groove.

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